

In re Application of:

Fastow et al.

Serial No.: 10/658,936

Filed:

September 9, 2003

For:

FLASH MEMORY WITH HIGH-K DIELECTRIC MATERIAL BETWEEN SUBSTRATE AND GATE

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450 Examiner:

NGUYEN, D.

Art Unit:

2818

Confirmation No.: 3102

Do Not Enter Thanks,

AMENDMENT AND RESPONSE TO OFFICE ACTION

Dear Sir:

In response to the Office Action mailed July 27, 2006, please consider the following remarks and enter the following amendments. The claims are presented beginning on page 2 of this response. Remarks begin on page 6.